

PECVD Series

Uni-body Design Concept

Foot-print outstanding (ref 1.0m*1.0m)

Process Design Kits

Better process performance

Variable Plasma Discharge Gap

Better process performance

Temperature Control

Chamber liner, electrode temperature control
suitable for different process application

Advanced RF System

Electrode RF driven (13.56MHz and/or 400KHz)
for better process tuned and controlled, low stress

Cost or Performance Orientation

RF, Pump, Values etc. depending on requirements

Sample Handling Options

Open-Load or Load-Lock



Specification	Parameters
Wafer Size Range	4,6,8,12 inch or multi-wafers optional
Deposition Materials	Si-Based (α -Si:H/SiO ₂ /SiN _x /SiC etc.), etc.
Vacuum	Roots & Mechanical Pump
RF Power	Full Range 500-2000W, optional
Gas System	6 lines(Standard) or customized
Wafer Stage Temperature Range	From 20°C to 400°C, higher temperature optional
Non-Uniformity	Less than $\pm 5\%$ (Edge Exclusion)